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Smart High-Side Power Switch for Industrial Applications
Two Channels: 2 x 90mΩ
Status Feedback

Product Summary

Operating Voltage	V_{bb}	5.5...40V	
	Active channels	one	two parallel
On-state Resistance	R_{ON}	90mΩ	45mΩ
Nominal load current	$I_{L(NOM)}$	3.7A	7.4A
Current limitation	$I_{L(SCr)}$	12A	12A
Operating Temperature	T_a	-30 … +85°C	

Package

PG-DSO-12-9

Green Product (RoHS compliant)

General Description

- N channel vertical power MOSFET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS® technology.
- Providing embedded protective functions

Applications

- µC compatible high-side power switch with diagnostic feedback for 12V and 24V grounded loads in industrial applications
- All types of resistive, inductive and capacitve loads
- Most suitable for loads with high inrush currents, so as lamps
- Replaces electromechanical relays, fuses and discrete circuits

Basic Functions

- Very low standby current
- CMOS compatible input
- Improved electromagnetic compatibility (EMC)
- Fast demagnetization of inductive loads
- Stable behaviour at undervoltage
- Wide operating voltage range
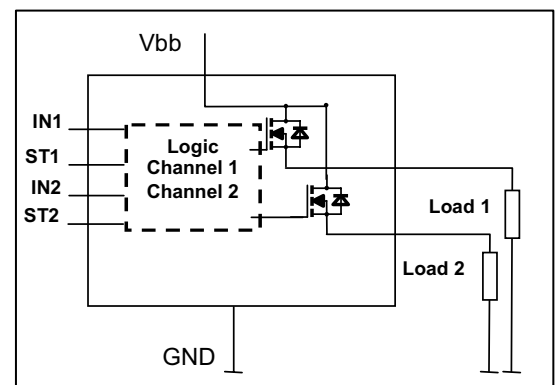- Logic ground independent from load ground

Protection Functions

- Short circuit protection
- Overload protection
- Current limitation
- Thermal shutdown
- Overvoltage protection (including load dump) with external resistor
- Reverse battery protection with external resistor
- Loss of ground and loss of V_{bb} protection
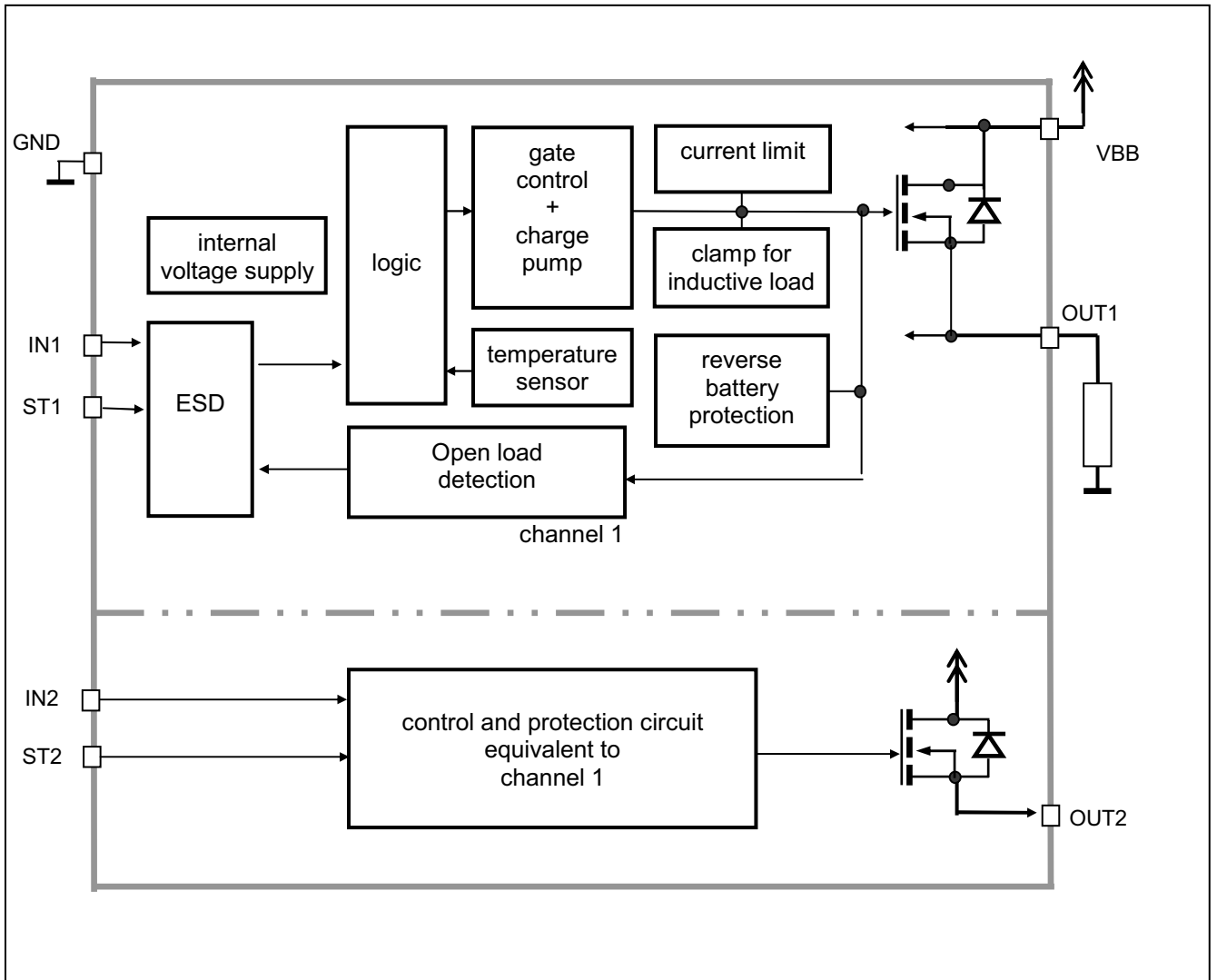- Electrostatic discharge protection (ESD)

Diagnostic Function

- Diagnostic feedback with open drain output
- Open load detection in OFF-state
- Feedback of thermal shutdown in ON-state
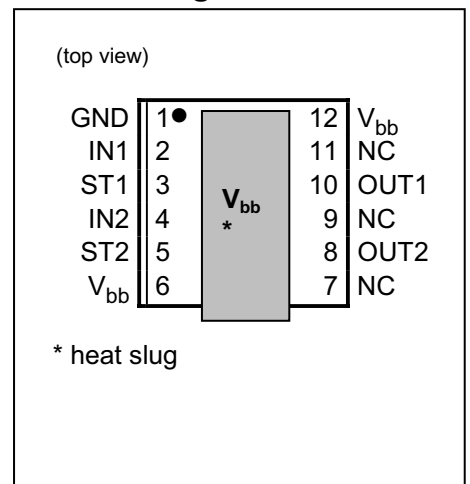
Block Diagram

Functional diagram

channel 1

GND

IN1

ST1

internal voltage supply

logic

ESD

gate control + charge pump

current limit

clamp for inductive load

temperature sensor

reverse battery protection

Open load detection

VBB

OUT1

IN2

ST2

control and protection circuit equivalent to channel 1

OUT2

Pin Definitions and Functions

Pin	Symbol	Function
1	GND	**Ground** of chip
2	IN1	**Input 1,2** activates channel 1,2 in case of logic high signal
4	IN2	
3	ST1	**Diagnostic feedback 1 & 2** of channel 1,2 open drain, low on failure
5	ST2	
6,12, heat slug	V_{bb}	**Positive power supply voltage**. Design the wiring for the simultaneous max. short circuit currents from channel 1 to 2 and also for low thermal resistance
7,9,11	NC	**Not Connected**
8	OUT2	**Output 1,2** protected high-side power output of channel 1 and 2. Design the wiring for the max. short circuit current
10	OUT1	

Pin configuration

(top view)

GND	1●	12	V_{bb}
IN1	2	11	NC
ST1	3	10	OUT1
IN2	4	9	NC
ST2	5	8	OUT2
V_{bb}	6	7	NC

V_{bb}
*

* heat slug

Maximum Ratings   at T_j = 25°C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 5)	V_{bb}	43	V
Supply voltage for full short circuit protection $T_{j,start}$ = -40 ...+150°C	V_{bb}	36	V
Load current (Short-circuit current, see page 6)	I_L	self-limited	A
Load dump protection[1] $V_{LoadDump} = V_A + V_s$, V_A = 13.5 V R_l[2] = 2 Ω, t_d = 400 ms; IN = low or high, each channel loaded with R_L = 13.5 Ω,	$V_{Load dump}$[3]	60	V
Junction temperature Operating temperature range Storage temperature range	T_j T_a T_{stg}	+150 -30 ...+85 -40 … +105	°C
Power dissipation (DC)[4] T_a = 25°C: (all channels active) T_a = 85°C:	P_{tot}	3.1 1.6	W
Maximal switchable inductance, single pulse V_{bb} = 12V, $T_{j,start}$ = 150°C[4], see diagrams on page 9 I_L = 3.5 A, E_{AS} = 178 mJ, 0Ω one channel: I_L = 7.0 A, E_{AS} = 337 mJ, 0Ω two parallel channels:	Z_L	21.3 10	mH
Electrostatic discharge capability (ESD) IN: (Human Body Model) ST: out to all other pins shorted: acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993 R=1.5kΩ; C=100pF	V_{ESD}	1.0 4.0 8.0	kV
Input voltage (DC) see internal circuit diagram page 8 Current through input pin (DC) Pulsed current through input pin[5] Current through status pin (DC)	V_{IN} I_{IN} I_{INp} I_{ST}	-10 ... +16 ±0.3 ±5.0 ±5.0	V mA

---

[1]   Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins (a 150Ω resistor for the GND connection is recommended.

[2] R_l = internal resistance of the load dump test pulse generator

[3] $V_{Load dump}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

[4]   Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm^2 (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air. See page 13

[5]   only for testing

n##Thermal Characteristics

Parameter and Conditions	Symbol	Values			Unit
		min	typ	max	
Thermal resistance					K/W
junction - Case[6] each channel:	R_{thjC}	--	--	5	
junction – ambient[6]	R_{thja}	--	--	--	
@ 6 cm² cooling area one channel active:		--	45	--	
all channels active:		--	40	--	

Electrical Characteristics

Parameter and Conditions, each of the four channels at T_j = -40...+150°C, V_{bb} = 12 V unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

Load Switching Capabilities and Characteristics

Parameter and Conditions	Symbol	min	typ	max	Unit
On-state resistance (V_{bb} to OUT); I_L = 2 A					mΩ
each channel, T_j = 25°C:	R_{ON}	--	70	90	
T_j = 150°C:		--	140	180	
two parallel channels, T_j = 25°C:		--	35	45	
see diagram, page 10					
Nominal load current one channel active:	$I_{L(NOM)}$	3.7	4.7	--	A
two parallel channels active:		7.4	9.5		
Device on PCB[6], T_a = 85°C, $T_j \le$ 150°C					
Output current while GND disconnected or pulled up[7]; Vbb = 32 V, V_{IN} = 0, see diagram page 8	$I_{L(GNDhigh)}$	--	--	2	mA
Turn-on time[8] IN ⌐ to 90% V_{OUT}:	t_{on}	--	100	250	µs
Turn-off time IN ⌐ to 10% V_{OUT}:	t_{off}	--	100	270	
R_L = 12 Ω					
Slew rate on[8] 10 to 30% V_{OUT}, R_L = 12 Ω:	dV/dt_{on}	0.2	--	1.0	V/µs
Slew rate off[8] 70 to 40% V_{OUT}, R_L = 12 Ω:	$-dV/dt_{off}$	0.2	--	1.1	V/µs

[6] Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70µm thick) copper area for V_{bb} connection. PCB is vertical without blown air. See page 13
[7] not subject to production test, specified by design
[8] See timing diagram on page 11.

Data Sheet 4 Rev. 1.1, 2008-10-07

Parameter and Conditions, each of the four channels at T_j = -40...+150°C, V_{bb} = 12 V unless otherwise specified	Symbol	Values			Unit
		min	typ	max	
Operating Parameters					
Operating voltage	$V_{bb(on)}$	5.5	--	40	V
Undervoltage switch off[9] T_j =-40°C...25°C:	$V_{bb(u\,so)}$	--	--	4.5	V
T_j =125°C:		--	--	4.5[10]	
Overvoltage protection[11] I_{bb} = 40 mA	$V_{bb(AZ)}$	41	47	52	V
Standby current[12] T_j =-40°C...25°C:	$I_{bb(off)}$	--	4.5	10	µA
V_{IN} = 0; see diagram page 11 T_j =150°C:		--	--	15	
T_j =125°C:		--	--	10[10]	
Off-State output current (included in $I_{bb(off)}$) V_{IN} = 0; each channel	$I_{L(off)}$	--	1	5	µA
Operating current [13], V_{IN} = 5V,	I_{GND}				mA
one channel on:		--	0.6	1.2	
all channels on:		--	1.2	2.4	
Protection Functions[14]					
Current limit, V_{out} = 0V, (see timing diagrams, page 11)	$I_{L(lim)}$				A
T_j =-40°C:		--	--	23	
T_j =25°C:		--	15		
T_j =+150°C:		9	--	----	
Repetitive short circuit current limit, $T_j = T_{jt}$ each channel	$I_{L(SCr)}$	--	12	--	A
two channels		--	12	--	
(see timing diagrams, page 11)					
Initial short circuit shutdown time $T_{j,start}$ =25°C: V_{out} = 0V (see timing diagrams on page 11)	$t_{off(SC)}$	--	2	--	ms
Output clamp (inductive load switch off)[15] at $V_{ON(CL)}$ = V_{bb} - V_{OUT}, I_L= 40 mA	$V_{ON(CL)}$	41	47	52	V
Thermal overload trip temperature	T_{jt}	150	--	--	°C
Thermal hysteresis	ΔT_{jt}	--	10	--	K

[9] is the voltage, where the device doesn´t change it´s switching condition for 15ms after the supply voltage falling below the lower limit of Vbb(on)

[10] not subject to production test, specified by design

[11] Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins (a 150Ω resistor for the GND connection is recommended). See also $V_{ON(CL)}$ in table of protection functions and circuit diagram on page 8.

[12] Measured with load; for the whole device; all channels off

[13] Add I_{ST}, if I_{ST} > 0

[14] Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

[15] If channels are connected in parallel, output clamp is usually accomplished by the channel with the lowest $V_{ON(CL)}$

Parameter and Conditions, each of the four channels at T_j = -40...+150°C, V_{bb} = 12 V unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

Reverse Battery

Parameter and Conditions	Symbol	min	typ	max	Unit
Reverse battery voltage [16]	$-V_{bb}$	--	--	32	V
Drain-source diode voltage ($V_{out} > V_{bb}$) I_L = -2.0 A, T_j = +150°C	$-V_{ON}$	--	600	--	mV

Diagnostic Characteristics

Parameter and Conditions	Symbol	min	typ	max	Unit
Open load detection voltage	$V_{OUT(OL)}$	1.7	2.8	4.0	V

Input and Status Feedback[17]

Parameter and Conditions	Symbol	min	typ	max	Unit
Input resistance (see circuit page 8)	R_I	2.5	4.0	6.0	kΩ
Input turn-on threshold voltage	$V_{IN(T+)}$	--	--	2.5	V
Input turn-off threshold voltage	$V_{IN(T-)}$	1.0	--	--	V
Input threshold hysteresis	$\Delta V_{IN(T)}$	--	0.2	--	V
Status change after positive input slope[18] with open load	$t_{d(STon)}$	--	10	20	μs
Status change after positive input slope[18] with overload	$t_{d(STon)}$	30	--	--	μs
Status change after negative input slope with open load	$t_{d(SToff)}$	--	--	500	μs
Status change after negative input slope[18] with overtemperature	$t_{d(SToff)}$	--	--	20	μs
Off state input current V_{IN} = 0.4 V:	$I_{IN(off)}$	5	--	20	μA
On state input current V_{IN} = 5 V:	$I_{IN(on)}$	10	35	60	μA
Status output (open drain) Zener limit voltage I_{ST} = +1.6 mA:	$V_{ST(high)}$	5.4	--	--	V
ST low voltage I_{ST} = +1.6 mA:	$V_{ST(low)}$	--	--	0.6	

---

[16] Requires a 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Power dissipation is higher compared to normal operating conditions due to the voltage drop across the drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 3 and circuit page 8).

[17] If ground resistors R_{GND} are used, add the voltage drop across these resistors.

[18] not subject to production test, specified by design

Truth Table

(each channel)

	IN	OUT	ST
Normal operation	L	L	H
	H	H	H
Open load	L	Z	L[19]
	H	H	H
Overtemperature	L	L	H
	H	L	L

L = "Low" Level   X = don't care   Z = high impedance, potential depends on external circuit
H = "High" Level   Status signal valid after the time delay shown in the timing diagrams

Parallel switching of channel 1 and 2 is easily possible by connecting the inputs and outputs in parallel (see truth table). If switching channel 1 to 2 in parallel, the status outputs ST1 and ST2 have to be configured as a 'Wired OR' function with a single pull-up resistor.

Terms
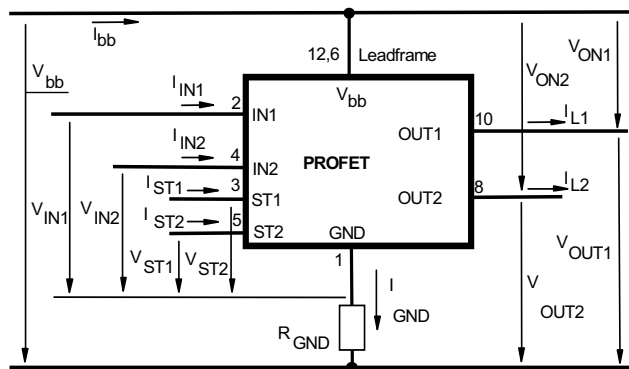
Leadframe (V_{bb}) is connected to pin 6,12
External R_{GND} optional; single resistor $R_{GND} = 150\ \Omega$ for reverse battery protection up to the max. operating voltage.

[19] L, if potential at the Output exceeds the OpenLoad detection voltage

Input circuit (ESD protection), IN1 or IN2
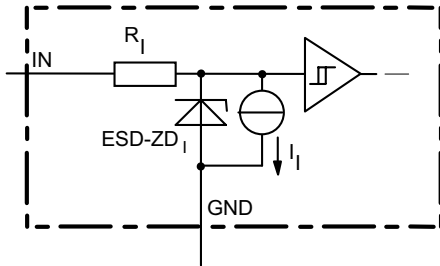
The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

Status output, ST1 or ST2
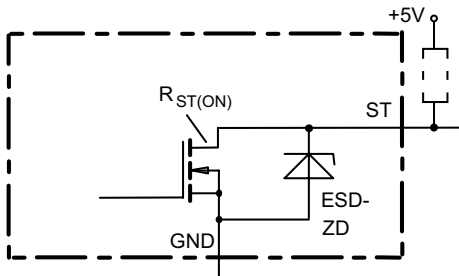
ESD-Zener diode: 6.1 V typ., max 0.3 mA; $R_{ST(ON)}$ < 375 Ω at 1.6 mA. The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

Inductive and overvoltage output clamp, OUT1 or OUT2
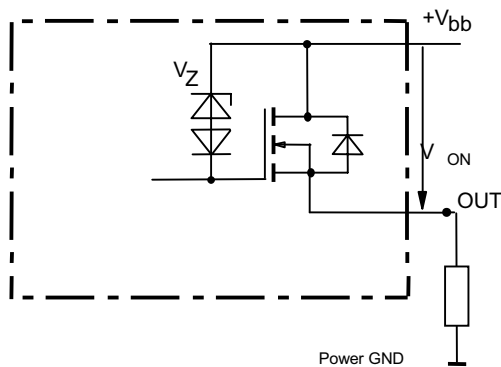
V_{ON} clamped to $V_{ON(CL)}$ = 47 V typ.

Overvolt. and reverse batt. protection
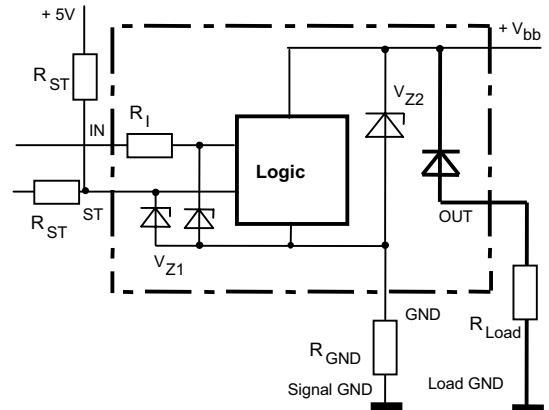
V_{Z1} = 6.1 V typ., V_{Z2} = 47 V typ., R_{GND} = 150 Ω, R_{ST} = 15 kΩ, R_I = 3.5 kΩ typ.
In case of reverse battery the load current has to be limited by the load. Temperature protection is not active

Open-load detection, OUT1 or OUT2

OFF-state diagnostic condition:
Open Load, if V_{OUT} > 3 V typ.; IN low
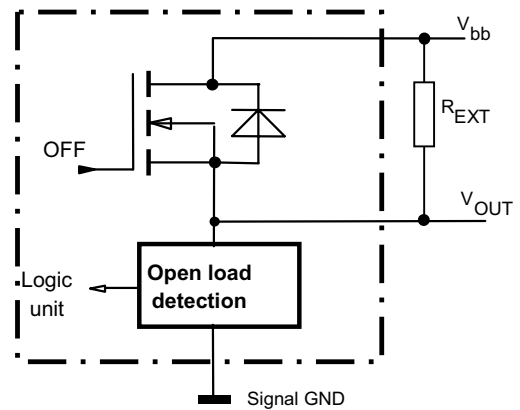
GND disconnect
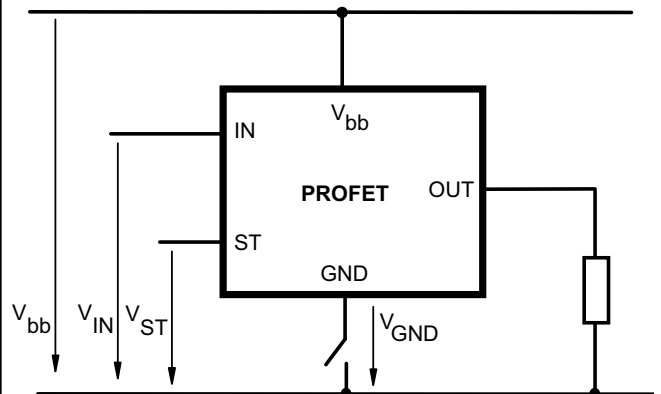
Any kind of load. In case of IN = high is $V_{OUT} \approx V_{IN} - V_{IN(T+)}$. Due to V_{GND} > 0, no V_{ST} = low signal available.

GND disconnect with GND pull up
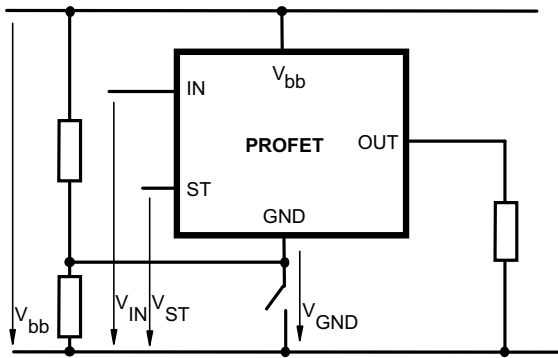
Any kind of load. If V_{GND} > V_{IN} - $V_{IN(T+)}$ device stays off
Due to V_{GND} > 0, no V_{ST} = low signal available.

V_{bb} disconnect with energized inductive load
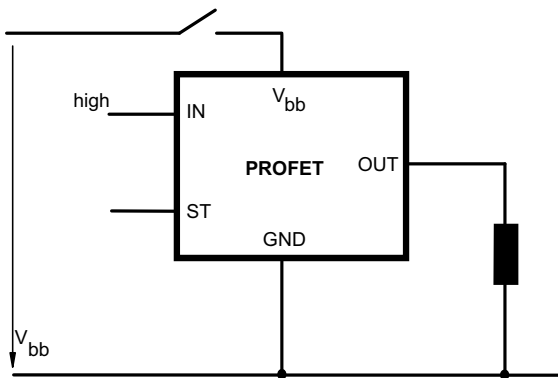
For inductive load currents up to the limits defined by Z_L (max. ratings and diagram on page 9) each switch is protected against loss of V_{bb}.

Consider at your PCB layout that in the case of Vbb disconnection with energized inductive load all the load current flows through the GND connection.

Inductive load switch-off energy dissipation
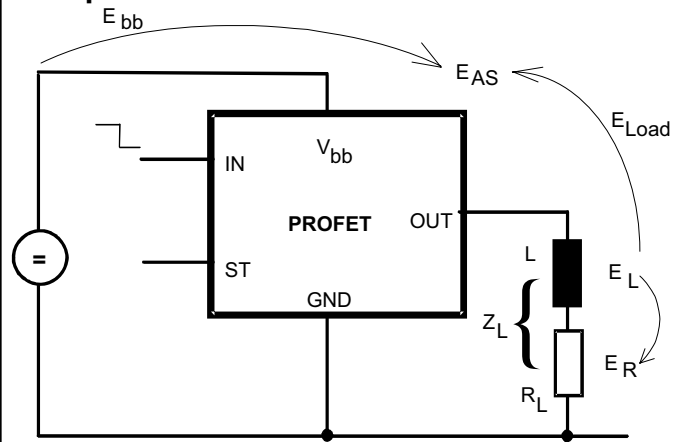
Energy stored in load inductance:

$$E_L = {}^1/_2 \cdot L \cdot I_L^2$$

While demagnetizing load inductance, the energy dissipated in PROFET is

$$E_{AS} = E_{bb} + E_L - E_R = \int V_{ON(CL)} \cdot i_L(t)\, dt,$$

with an approximate solution for $R_L > 0\,\Omega$:

$$E_{AS} = \frac{I_L \cdot L}{2 \cdot R_L}\,(V_{bb} + |V_{OUT(CL)}|)\ ln\,(1 + \frac{I_L \cdot R_L}{|V_{OUT(CL)}|})$$

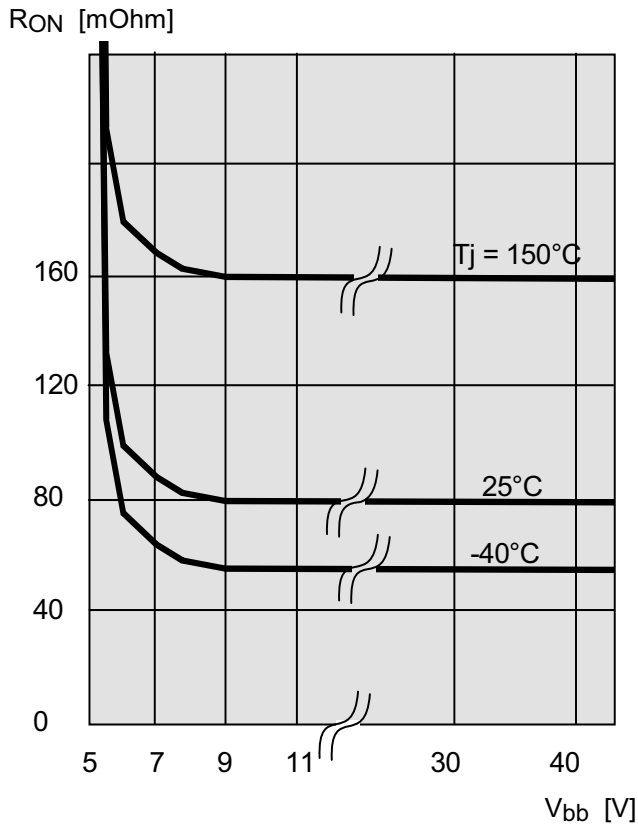## Maximum allowable load inductance for a single switch off (one channel)[4]
$L = f(I_L)$; $T_{j,start}$ = 150°C, V_{bb} = 12 V, R_L = 0 Ω
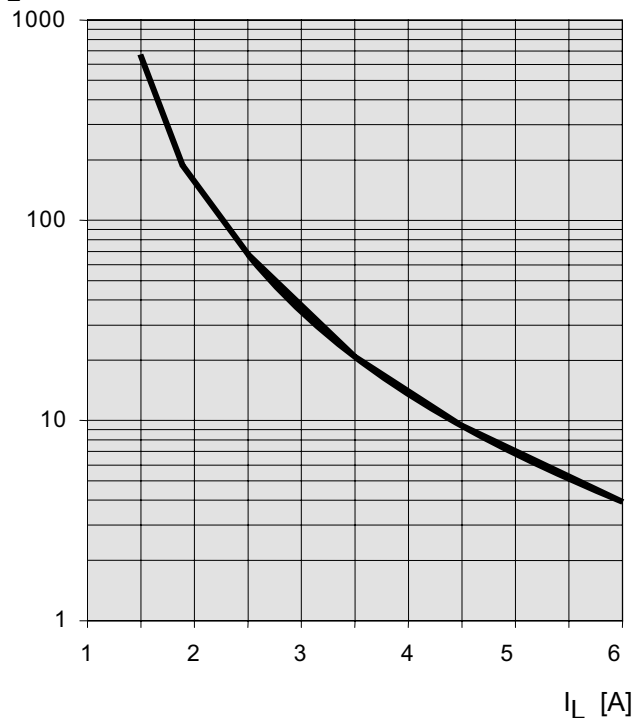
Typ. on-state resistance

$R_{ON} = f(V_{bb}, T_j)$; $I_L = 2\,A$, IN = high

R$_{ON}$ [mOhm]

Tj = 150°C

25°C

-40°C

160

120

80

40

0

5   7   9   11   30   40

V$_{bb}$ [V]

Typ. standby current

$I_{bb(off)} = f(T_j)$; V_{bb} = 9...34 V, IN1,2 = low

I$_{bb(off)}$ [µA]

45
40
35
30
25
20
15
10
5
0

-50   0   50   100   150   200

T$_j$ [°C]
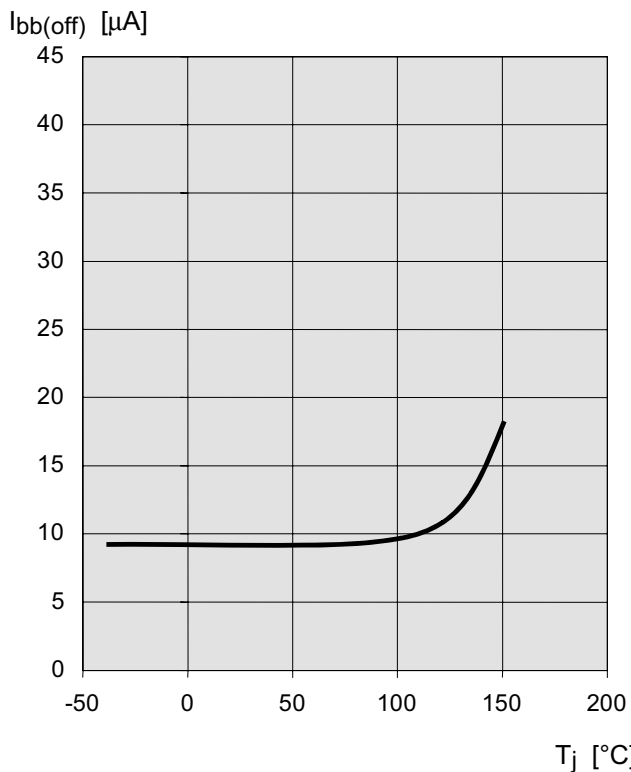
Timing diagrams

Both channels are symmetric and consequently the diagrams are valid for channel 1 and channel 2

Figure 1a: V_{bb} turn on:

Figure 2a: Switching a resistive load, turn-on/off time and slew rate definition:
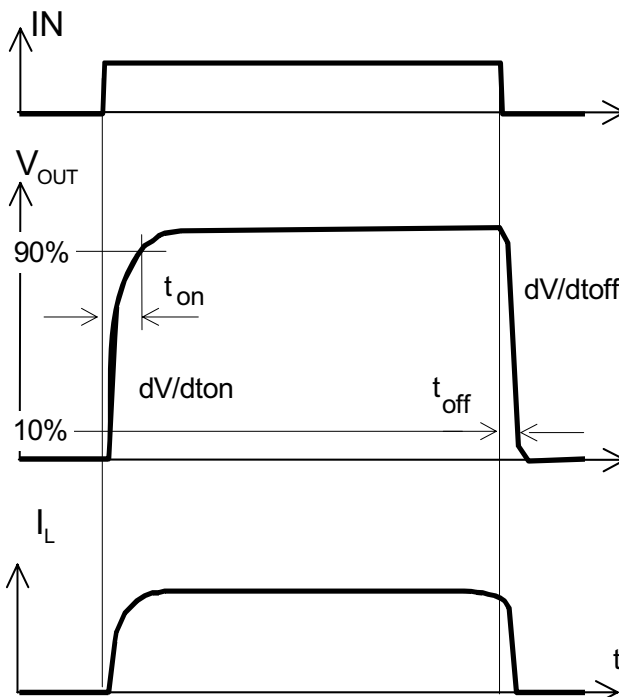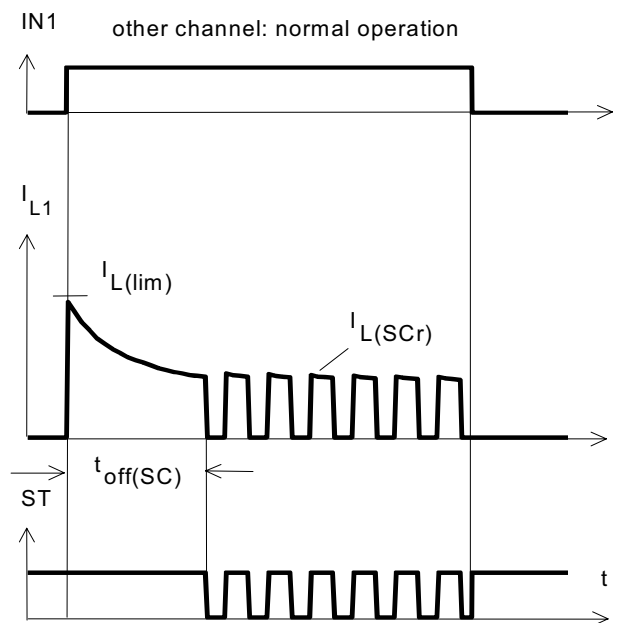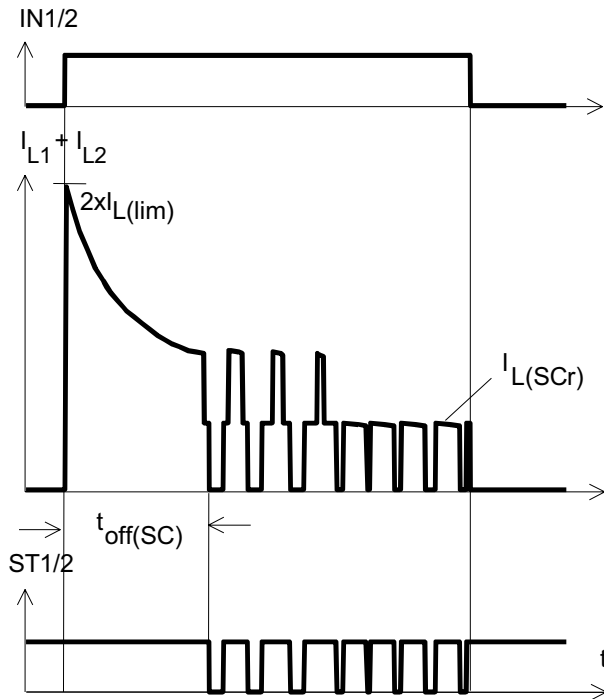

Figure 2b: Switching a lamp:

Figure 3a: Turn on into short circuit: shut down by overtemperature, restart by cooling

Heating up of the chip may require several milliseconds, depending on external conditions

Figure 3b: Turn on into short circuit: shut down by overtemperature, restart by cooling (two parallel switched channels 1 and 2)

ST1 and ST2 have to be configured as a 'Wired OR' function ST1/2 with a single pull-up resistor.
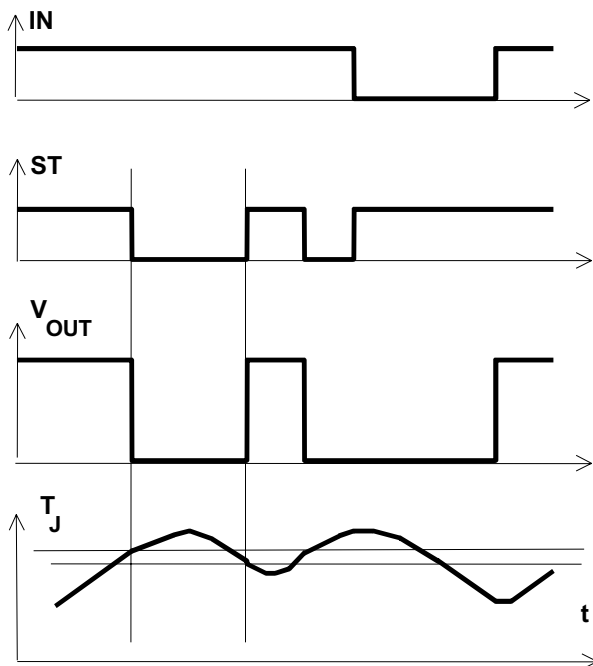
Figure 4a: Overtemperature: Reset if $T_j < T_{jt}$

Figure 5a: Open load: detection in OFF-state, turn on/off to open load
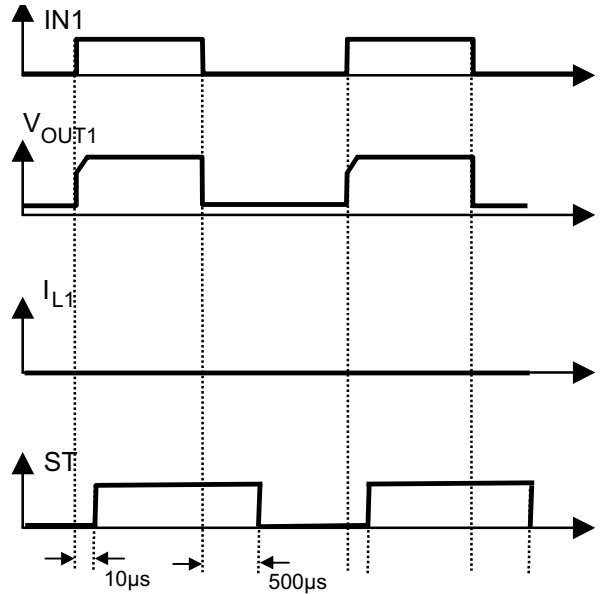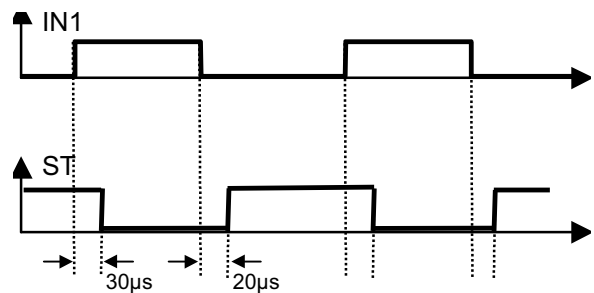Open load of channel 1; other channels normal operation

Figure 6a: Status change after, turn on/off to overtemperature
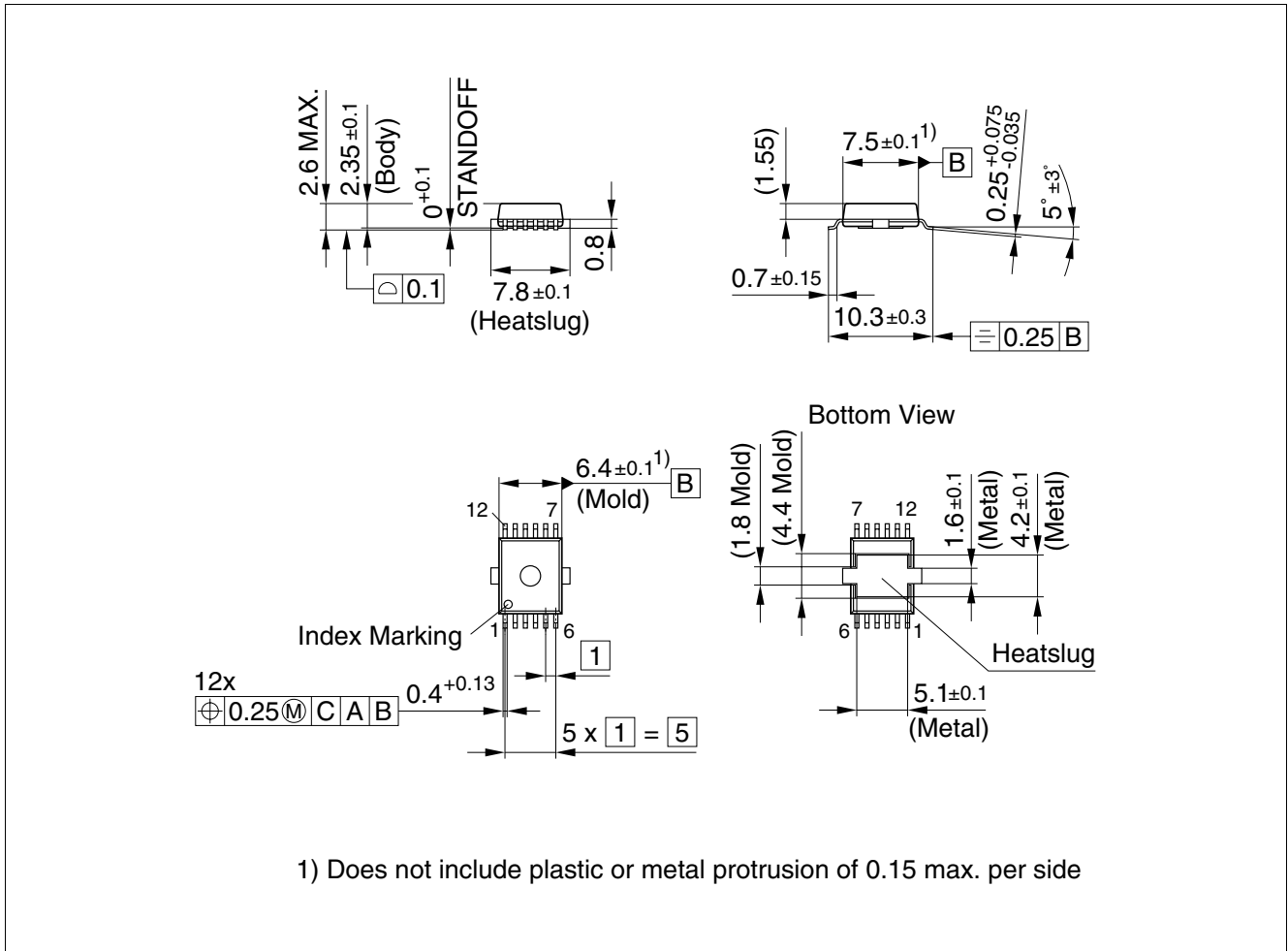Overtemperature of channel 1; other channels normal operation

1 Package Outlines

1) Does not include plastic or metal protrusion of 0.15 max. per side

Figure 1   PG-DSO-12-9

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

For further information on alternative packages, please visit our website:
http://www.infineon.com/packages.

Dimensions in mm

2 Revision History

Revision	Date	Changes
1.1	2008-10-07	RoHS-compliant DSO package version of the ITS724G All pages: Infineon logo updated Page 1: Added "RoHS" logo, added "Green Product (RoHS compliant)" statement to feature list, package names changed to RoHS compliant versions. Page 14: Package names changed to RoHS compliant versions, added "Green Product" description page 15: added Revision History page 16: added Legal Disclaimer

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